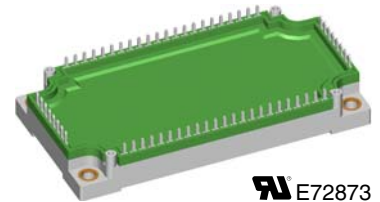
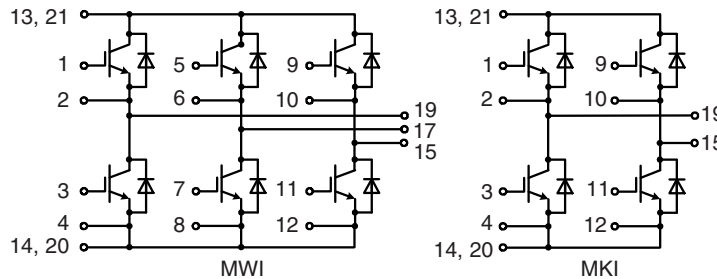


IGBT Modules Sixpack, H Bridge

Short Circuit SOA Capability
Square RBSOA

$$\begin{aligned} I_{C25} &= 165 \text{ A} \\ V_{CES} &= 1200 \text{ V} \\ V_{CE(sat) \text{ typ.}} &= 2.0 \text{ V} \end{aligned}$$



See outline drawing for pin arrangement

IGBTs		
Symbol	Conditions	Maximum Ratings
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	1200 V
V_{GES}		± 20 V
I_{C25}	$T_C = 25^{\circ}\text{C}$	165 A
I_{C80}	$T_C = 80^{\circ}\text{C}$	115 A
I_{CM}	$V_{GE} = \pm 15 \text{ V}; R_G = 12 \Omega; T_{VJ} = 125^{\circ}\text{C}$	200 A
V_{CEK}	RBSOA; clamped inductive load; $L = 100 \mu\text{H}$	V_{CES}
t_{SC}	$V_{CE} = 900 \text{ V}; V_{GE} = \pm 15 \text{ V}; R_G = 12 \Omega; T_{VJ} = 125^{\circ}\text{C}$ SCSOA; non-repetitive	10 μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	640 W

Features

- NPT³ IGBTs
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
 - short tail current for optimized performance also in resonant circuits
- HiPerFREDTM diode:
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
- Industry Standard Package
 - solderable pins for PCB mounting
 - isolated copper base plate

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 100 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.0 2.3	2.5 V V
$V_{GE(th)}$	$I_C = 4 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		1.4	1.4 mA mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			400 nA
$t_{d(on)}$	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 100 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 12 \Omega$		330	ns
t_r			15	ns
$t_{d(off)}$			750	ns
t_f			45	ns
E_{on}			12	mJ
E_{off}			10	mJ
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		7.4	nF
Q_{Gon}	$V_{CE} = 600 \text{ V}; V_{GE} = 15 \text{ V}; I_C = 150 \text{ A}$		0.76	μC
R_{thJC}	(per IGBT)			0.19 K/W

Typical Applications

- MWI
 - AC drives
 - power supplies with power factor correction
- MKI
 - motor control
 - . DC motor amature winding
 - . DC motor excitation winding
 - . synchronous motor excitation winding
 - supply of transformer primary winding
 - . power supplies
 - . welding
 - . X-ray
 - . battery charger

Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	200	A
I_{F80}	$T_C = 80^\circ\text{C}$	130	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 100\text{ A}; V_{GE} = 0\text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.3 1.7	2.6	V V
I_{RM} t_{rr}	$I_F = 120\text{ A}; di_F/dt = -750\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 600\text{ V}; V_{GE} = 0\text{ V}$		58 190	A ns
R_{thJC}	(per diode)			0.3 K/W

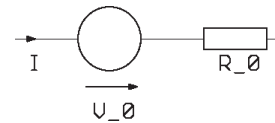
Module

Symbol	Conditions	Maximum Ratings	
T_{VJ}	operating	-40...+125	$^\circ\text{C}$
T_{JM}		+150	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
M_d	Mounting torque (M5)	3~6	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{pin-chip}$			1.8	m Ω
d_S	Creepage distance on surface	10		mm
d_A	Strike distance in air	10		mm
R_{thCH}	with heatsink compound		0.01	K/W
Weight			300	g

Equivalent Circuits for Simulation

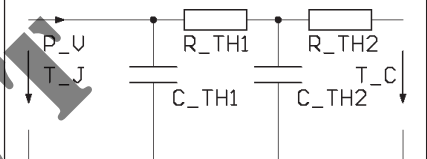
Conduction



IGBT (typ. at $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$)
 $V_0 = 0.95\text{ V}; R_0 = 14\text{ m}\Omega$

Free Wheeling Diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_0 = 1.27\text{ V}; R_0 = 4.3\text{ m}\Omega$

Thermal Response



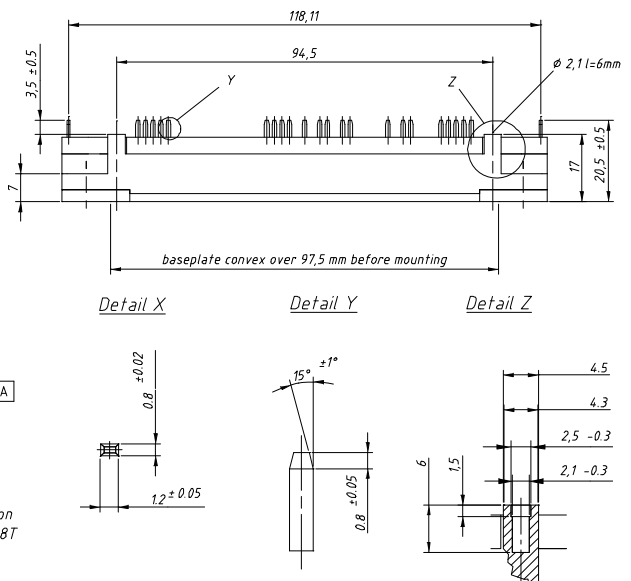
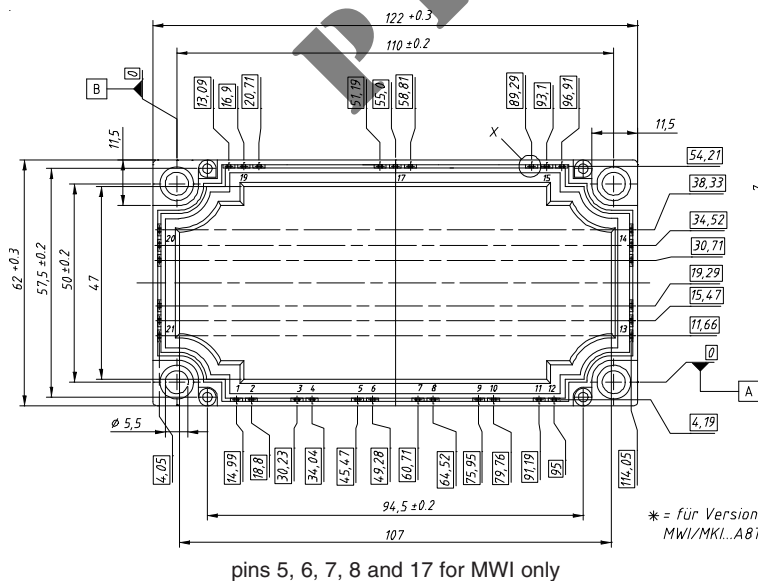
IGBT (typ.)

$C_{th1} = 0.389\text{ J/K}; R_{th1} = 0.139\text{ K/W}$
 $C_{th2} = 2.154\text{ J/K}; R_{th2} = 0.051\text{ K/W}$

Free Wheeling Diode (typ.)

$C_{th1} = 0.301\text{ J/K}; R_{th1} = 0.24\text{ K/W}$
 $C_{th2} = 2.005\text{ J/K}; R_{th2} = 0.062\text{ K/W}$

Dimensions in mm (1 mm = 0.0394")



IXYS reserves the right to change limits, test conditions and dimensions.

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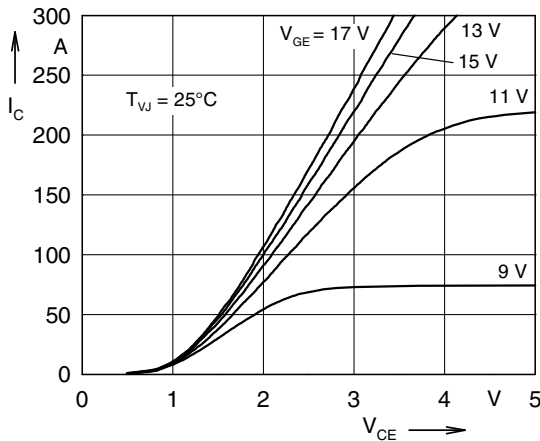


Fig. 1 Typ. output characteristics

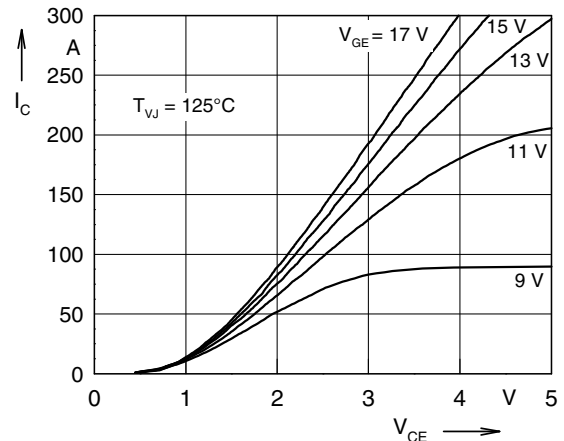


Fig. 2 Typ. output characteristics

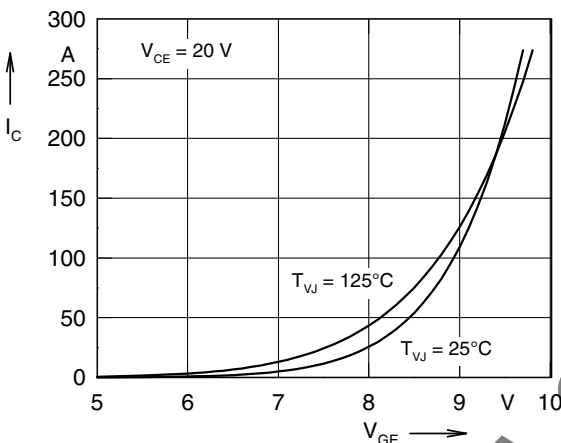


Fig. 3 Typ. transfer characteristics

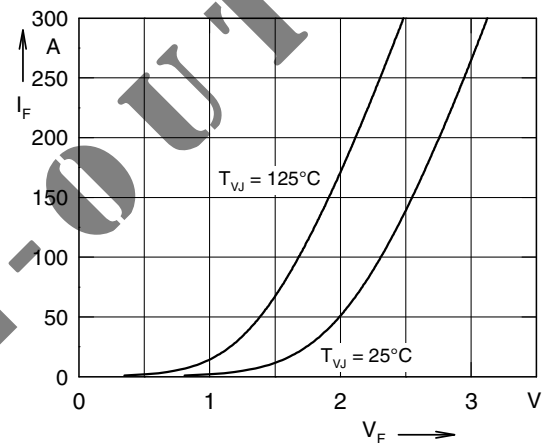


Fig. 4 Typ. forward characteristics of free wheeling diode

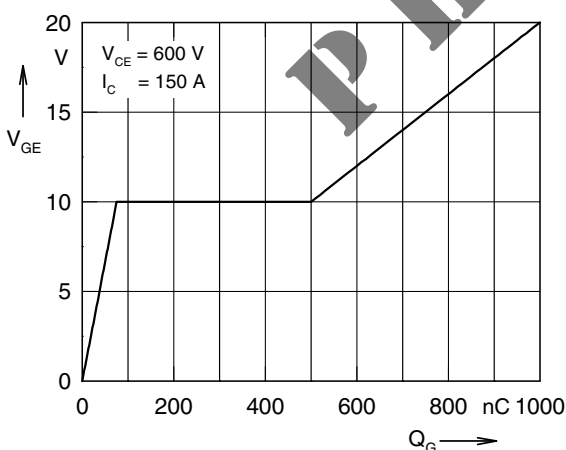


Fig. 5 Typ. turn on gate charge

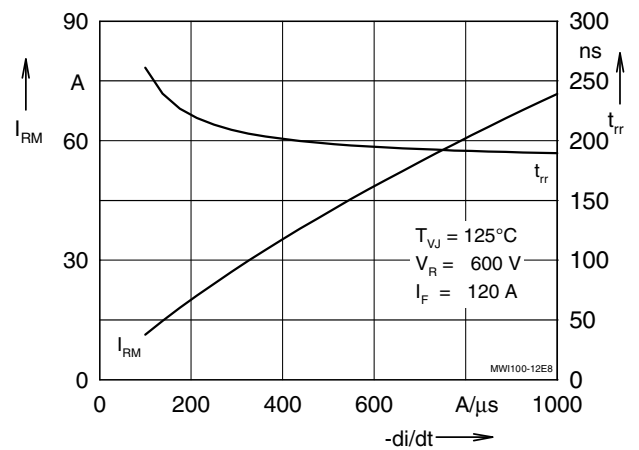


Fig. 6 Typ. turn off characteristics of free wheeling diode

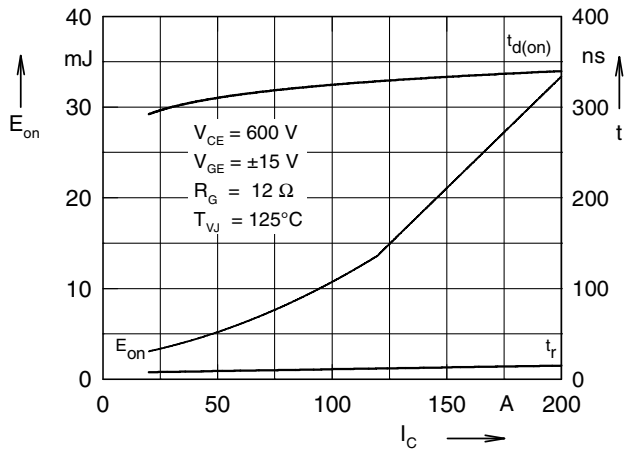


Fig. 7 Typ. turn on energy and switching times versus collector current

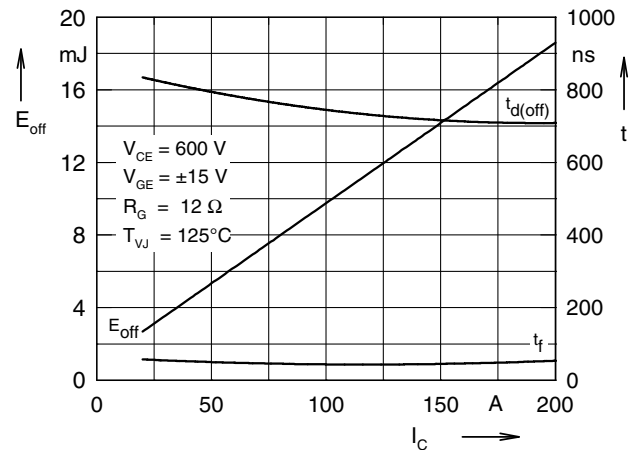


Fig. 8 Typ. turn off energy and switching times versus collector current

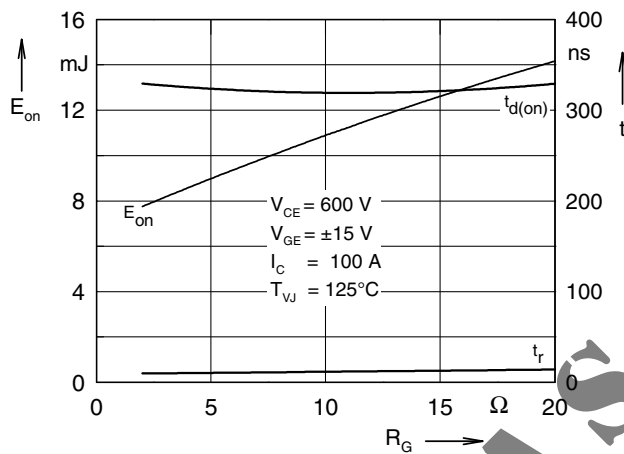


Fig. 9 Typ. turn on energy and switching times versus gate resistor

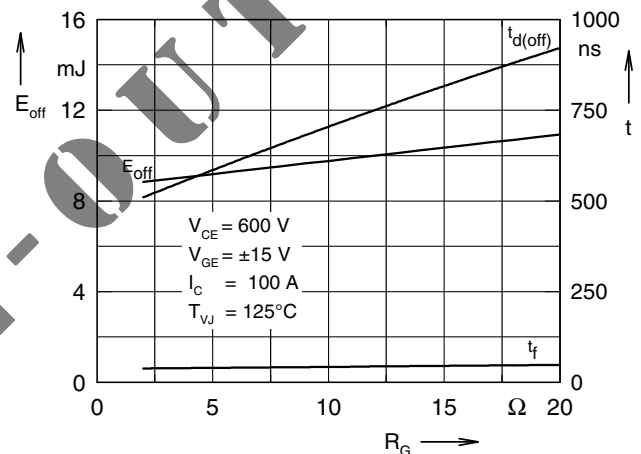


Fig. 10 Typ. turn off energy and switching times versus gate resistor

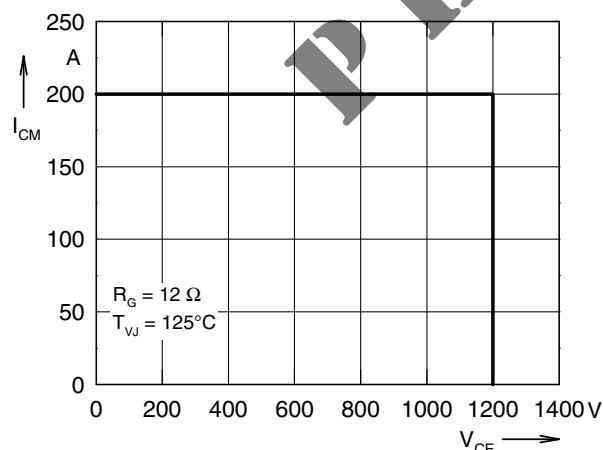


Fig. 11 Reverse biased safe operating area RBSOA

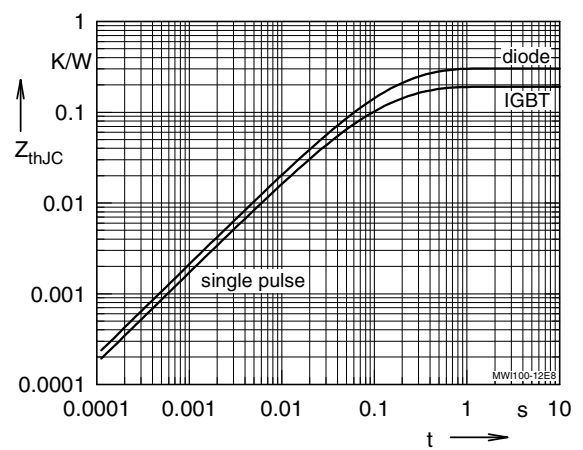


Fig. 12 Typ. transient thermal impedance